

Fig.1

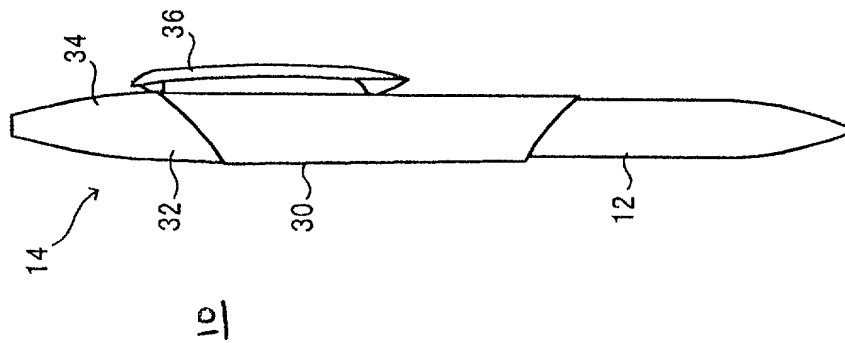


Fig.2

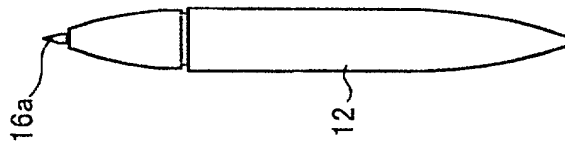


Fig.3

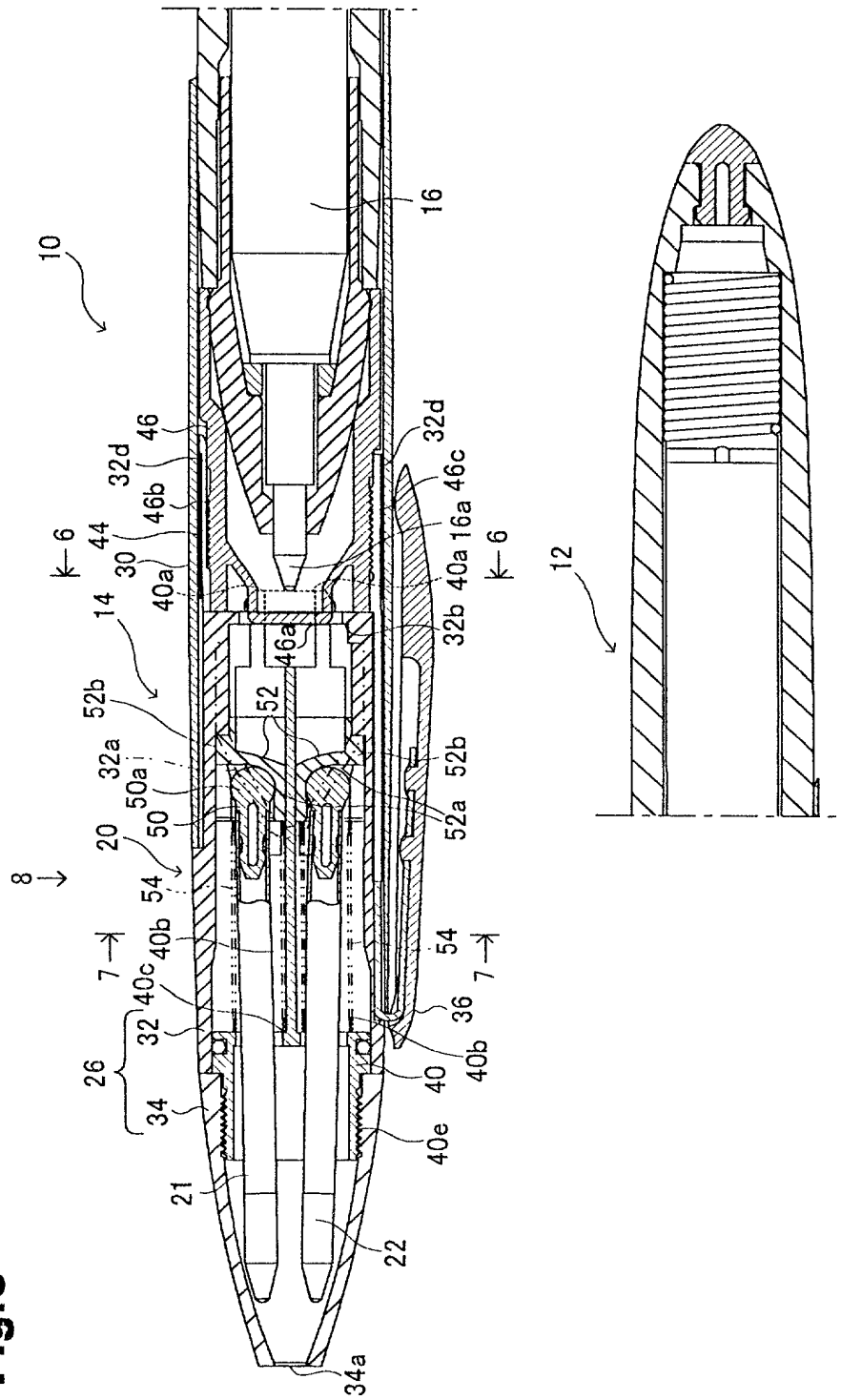


Fig.4

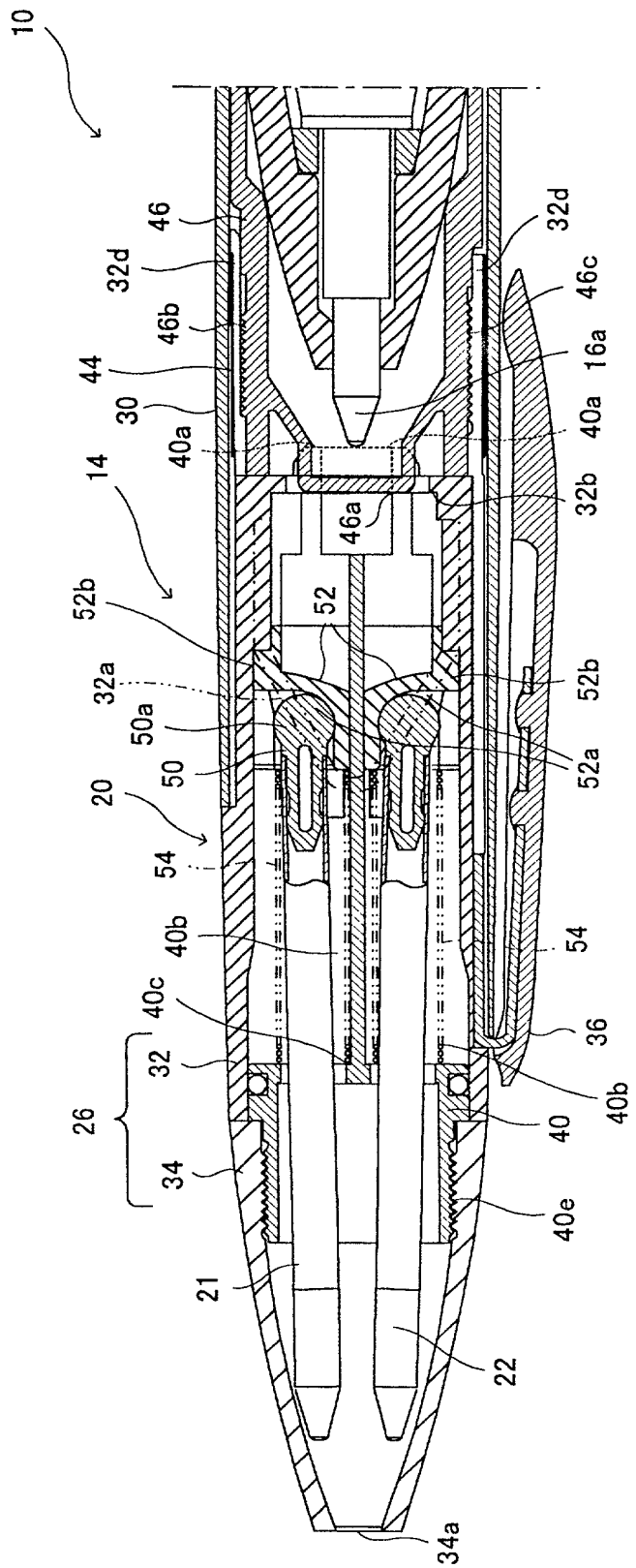


Fig.6

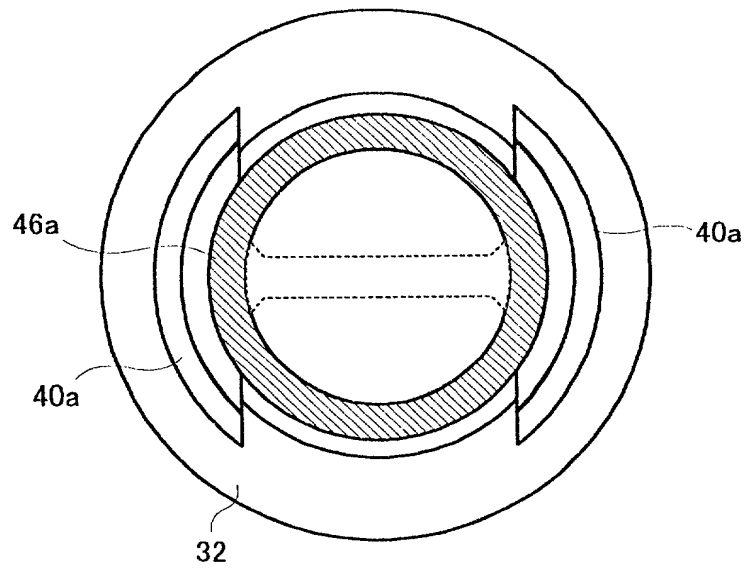


Fig.7

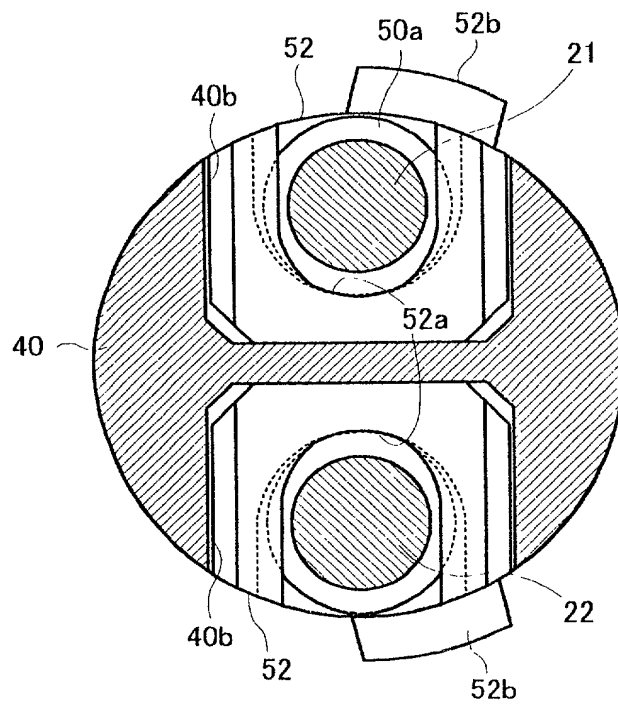


Fig.8

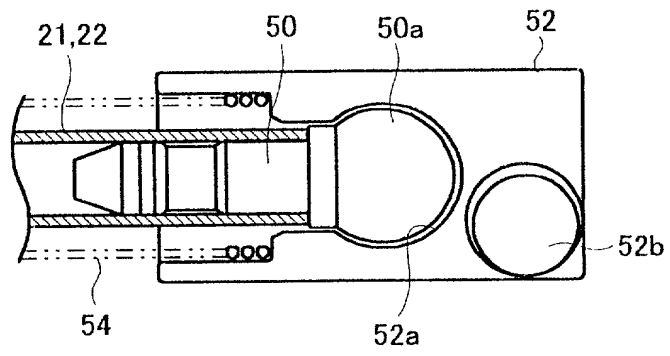


Fig.9

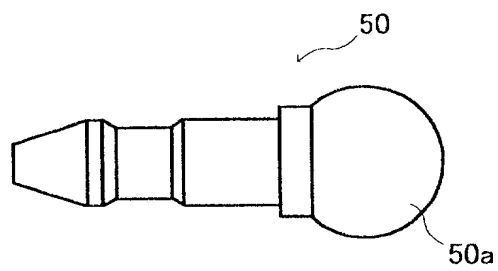


Fig. 10(a)

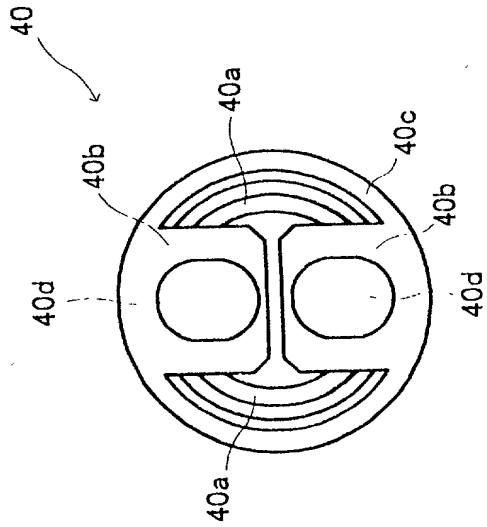
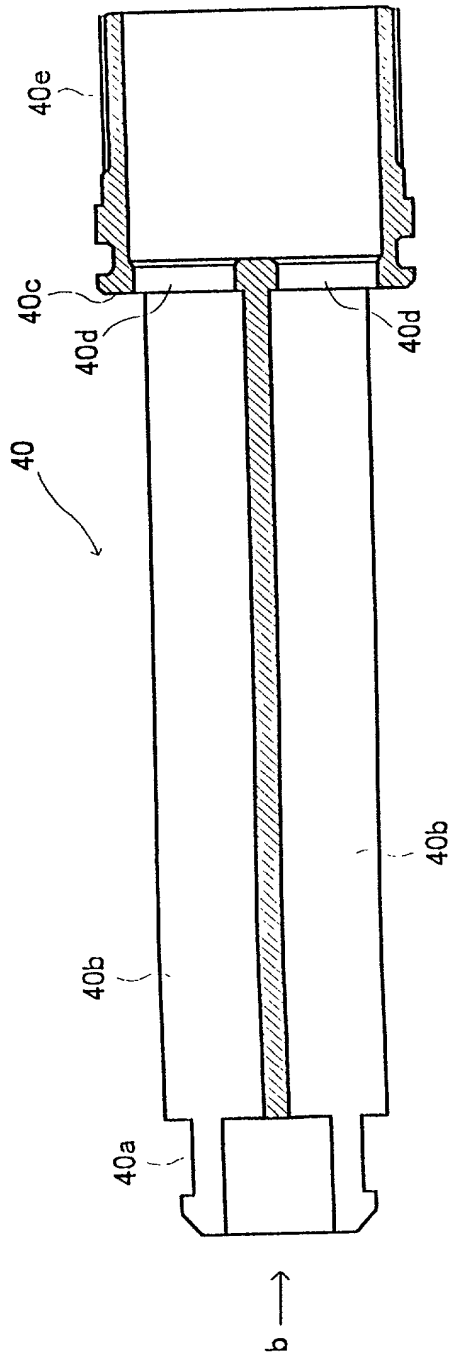


Fig. 10(b)

Fig.11

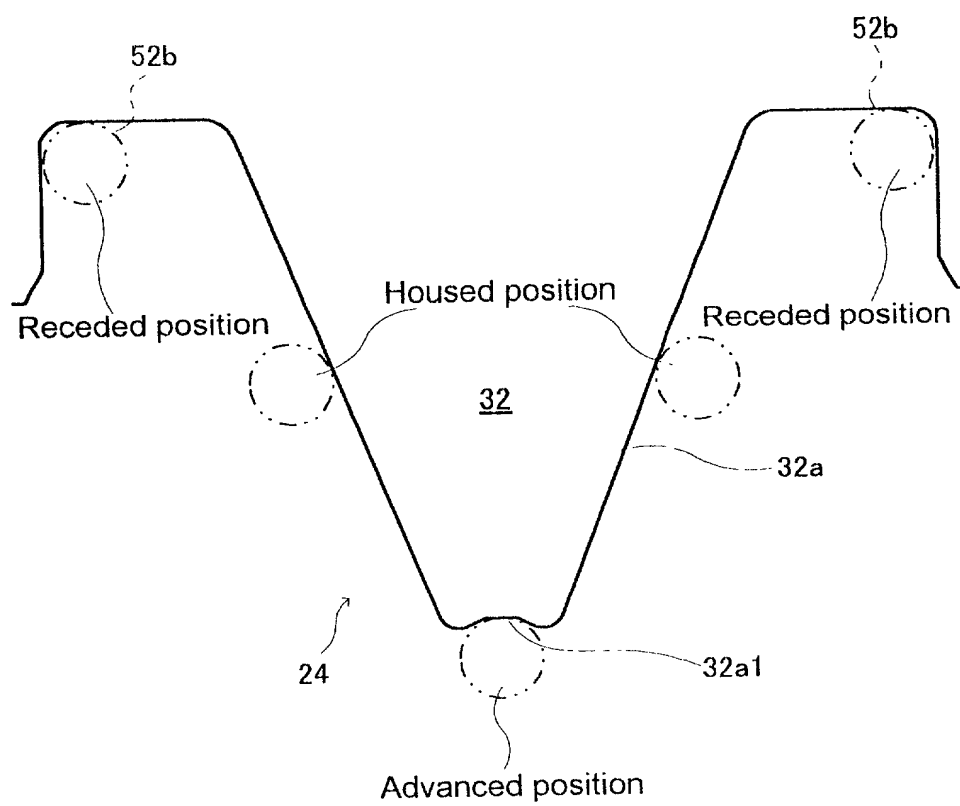


Fig. 12

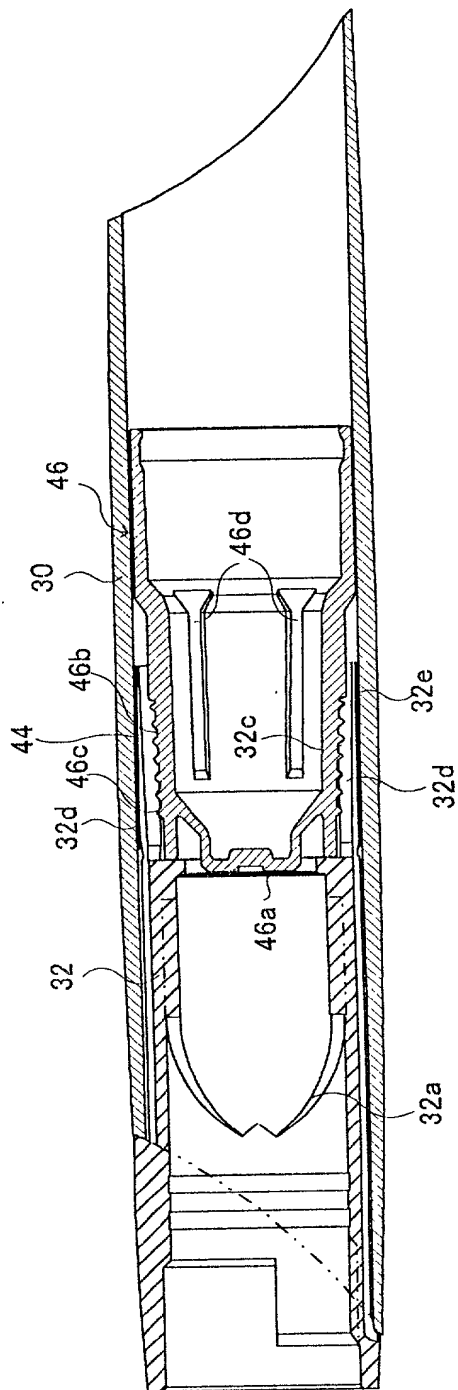


Fig.13(a)

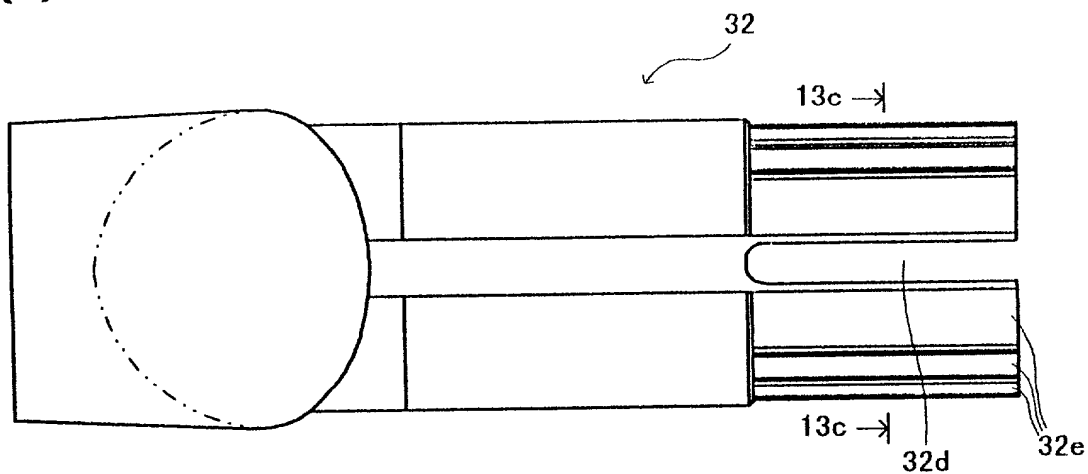


Fig.13(b)

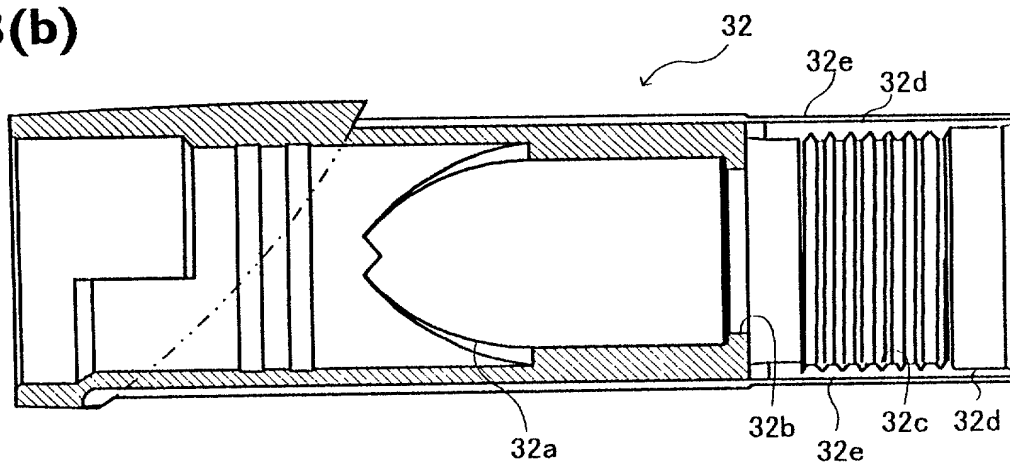


Fig.13(c)

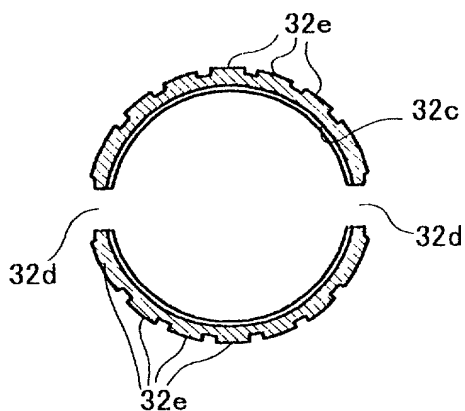


Fig. 14(a)

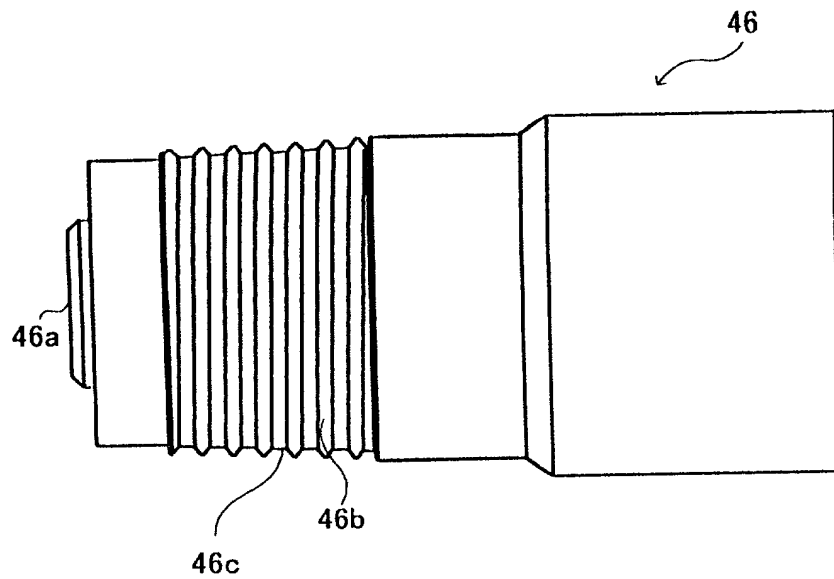


Fig. 14(b)

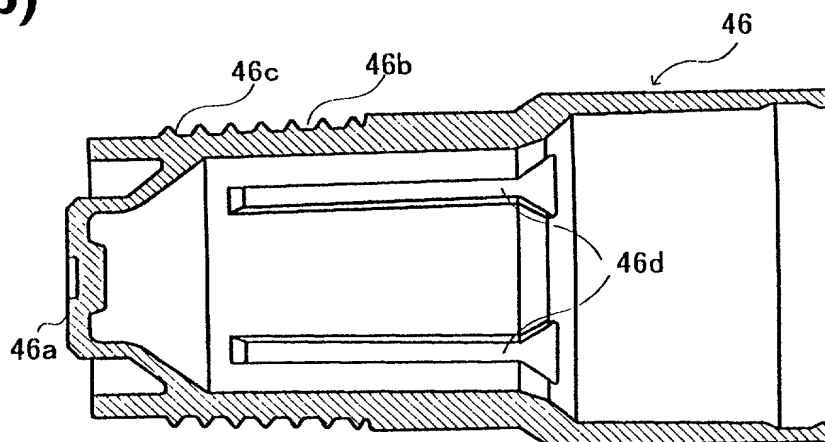


Fig. 15

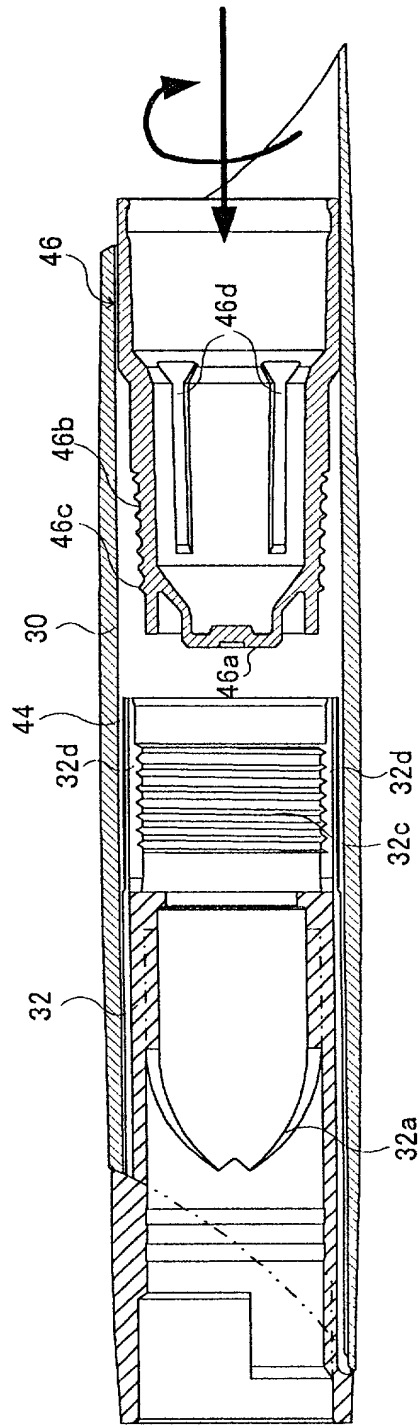


Fig. 16

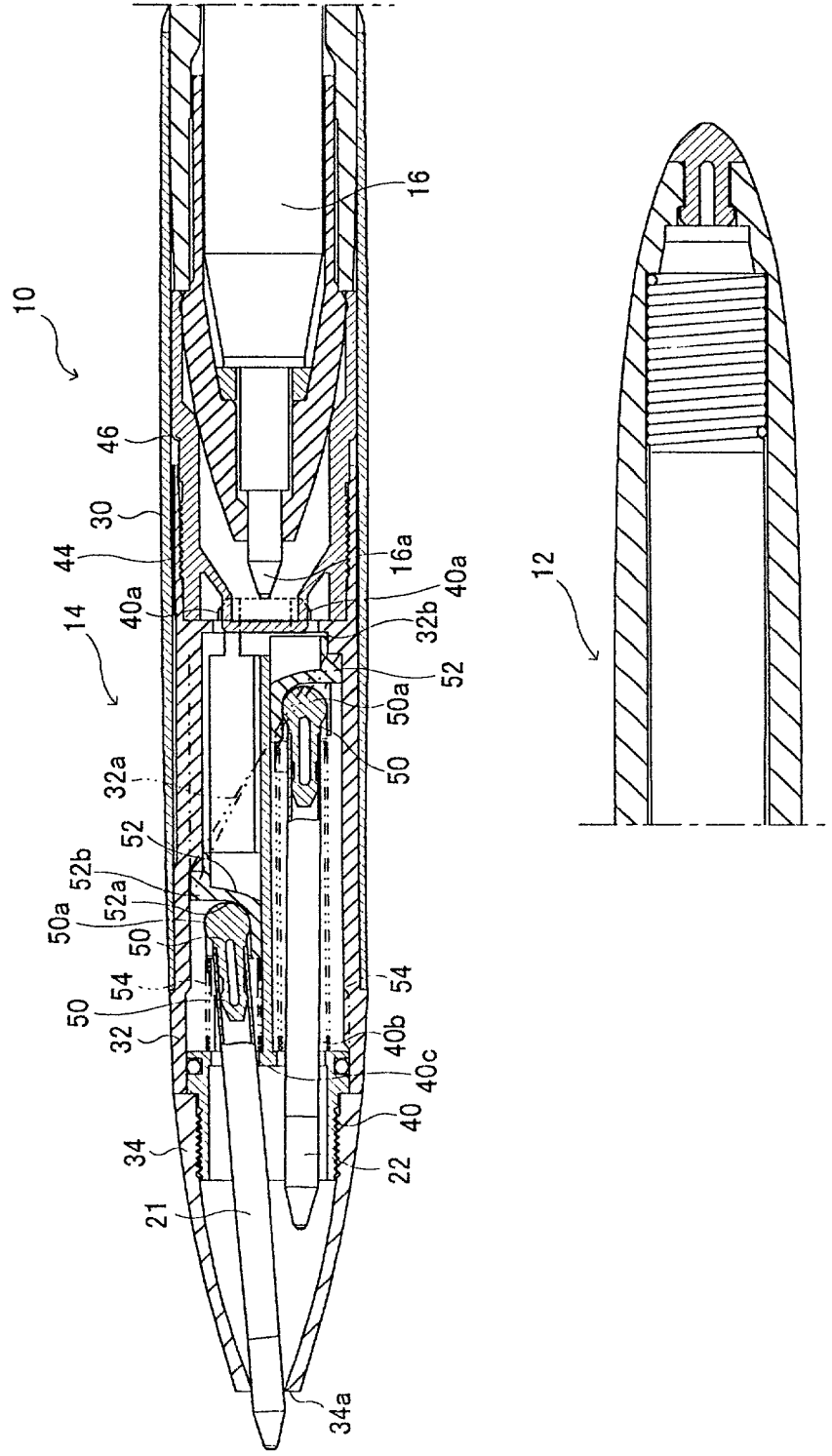


Fig. 18

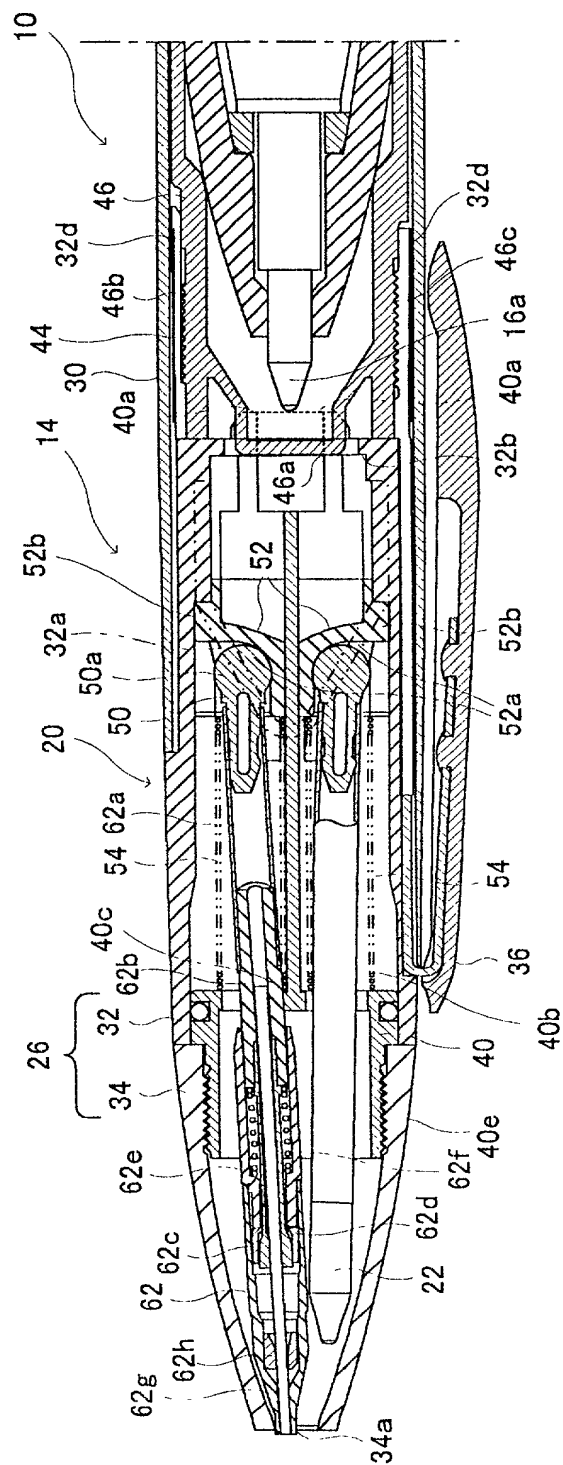


Fig.19

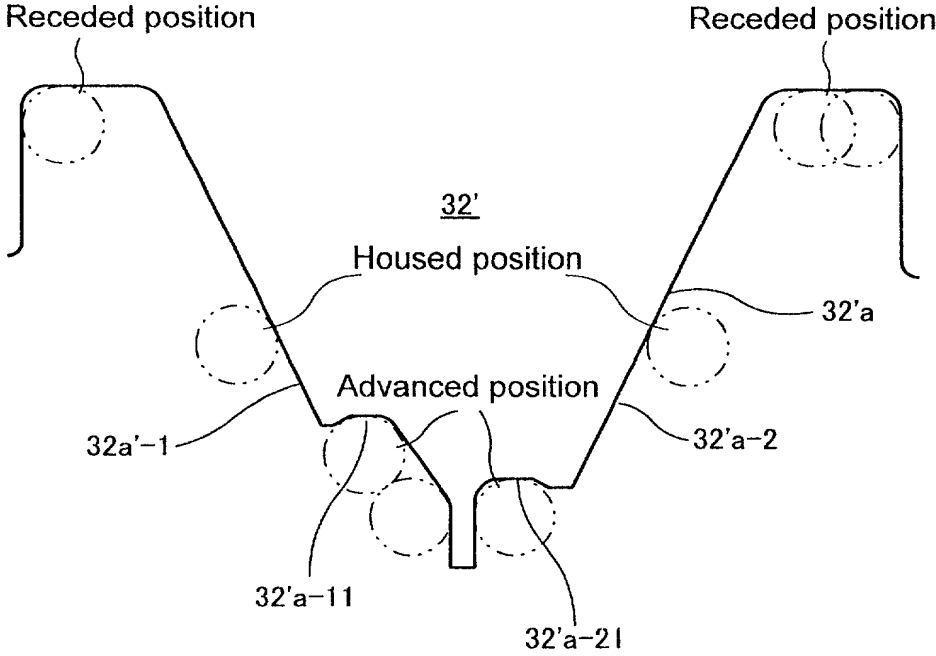


Fig.20

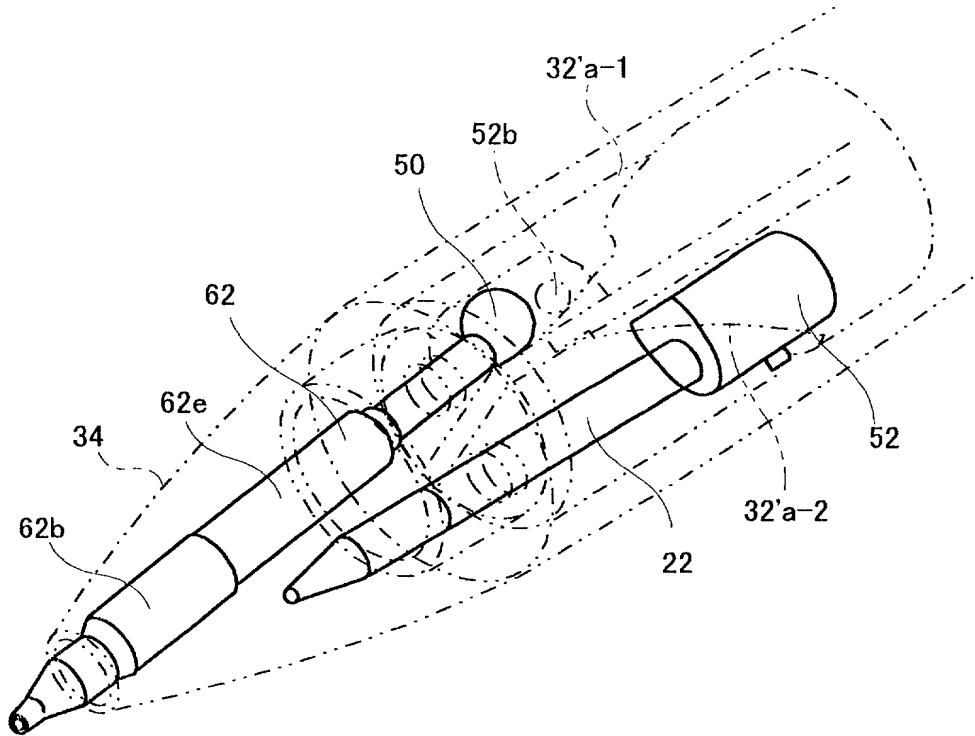


Fig.21

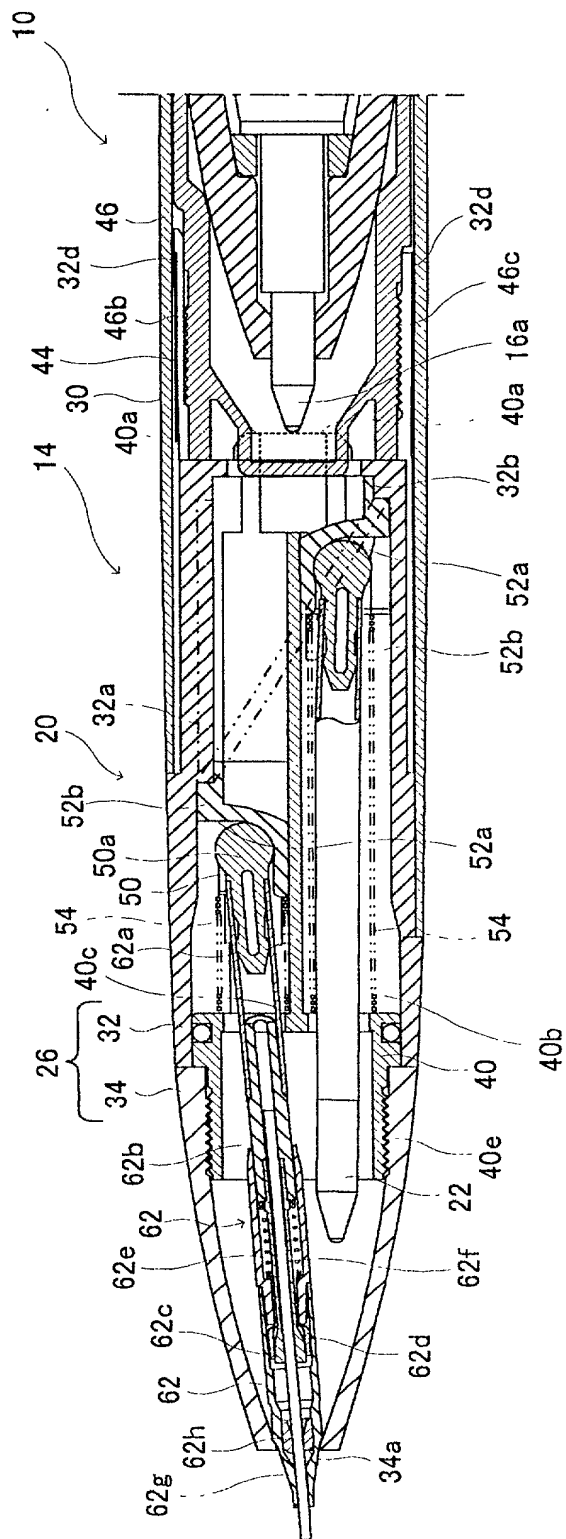


FIG. 23 is a cross-sectional view of a device in a first state, showing a first component 32-1 and a second component 32a. The device includes a first layer 46a, a second layer 46b, and a third layer 46c. A first opening 46d is formed in the first layer 46a, and a second opening 46e is formed in the second layer 46b. The first component 32-1 is positioned in the first opening 46d, and the second component 32a is positioned in the second opening 46e. The device is shown in a first state, where the first component 32-1 is in contact with the second component 32a.

Fig.23

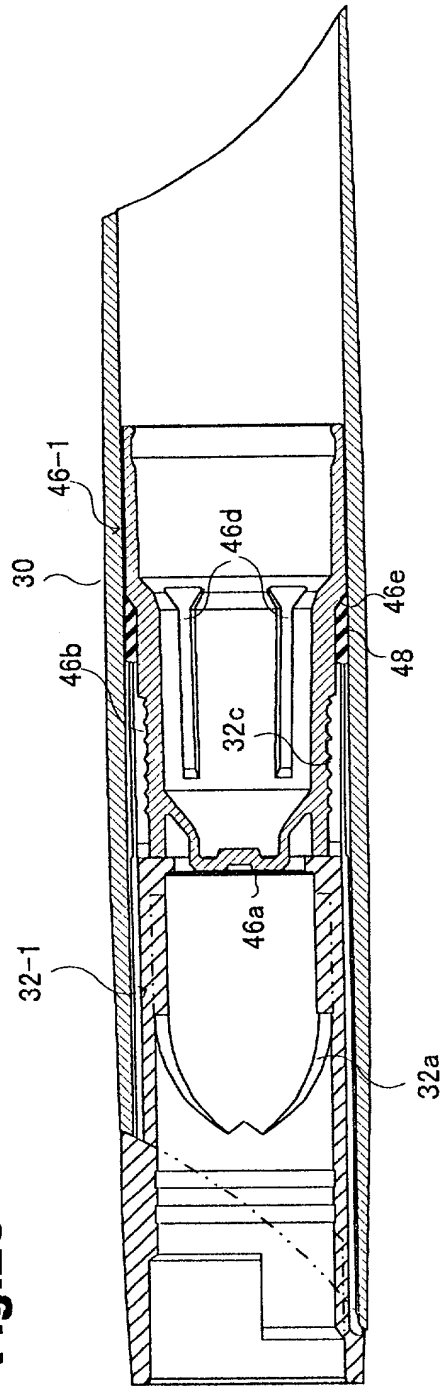


Fig.24

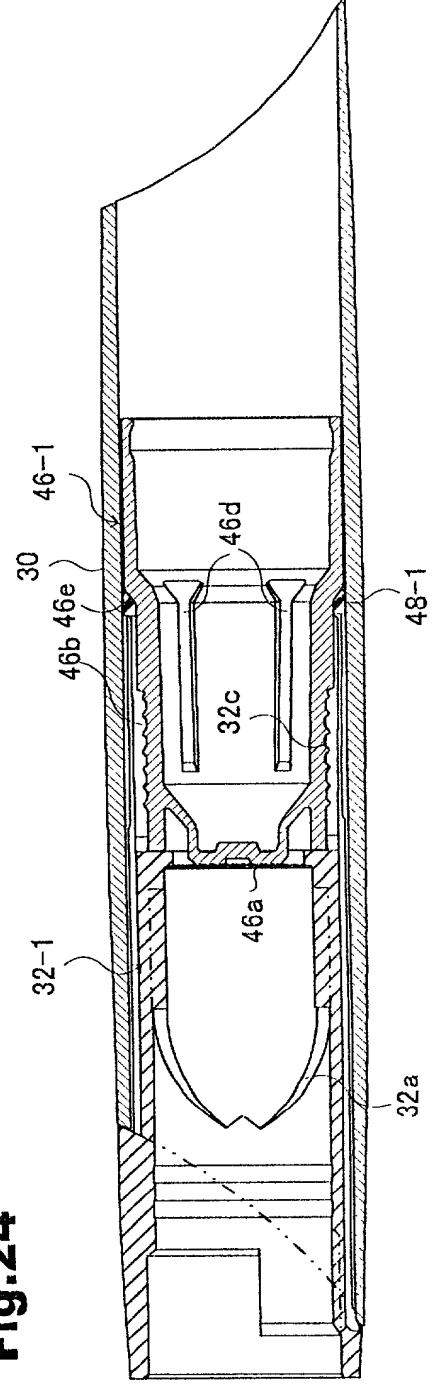


Fig. 25

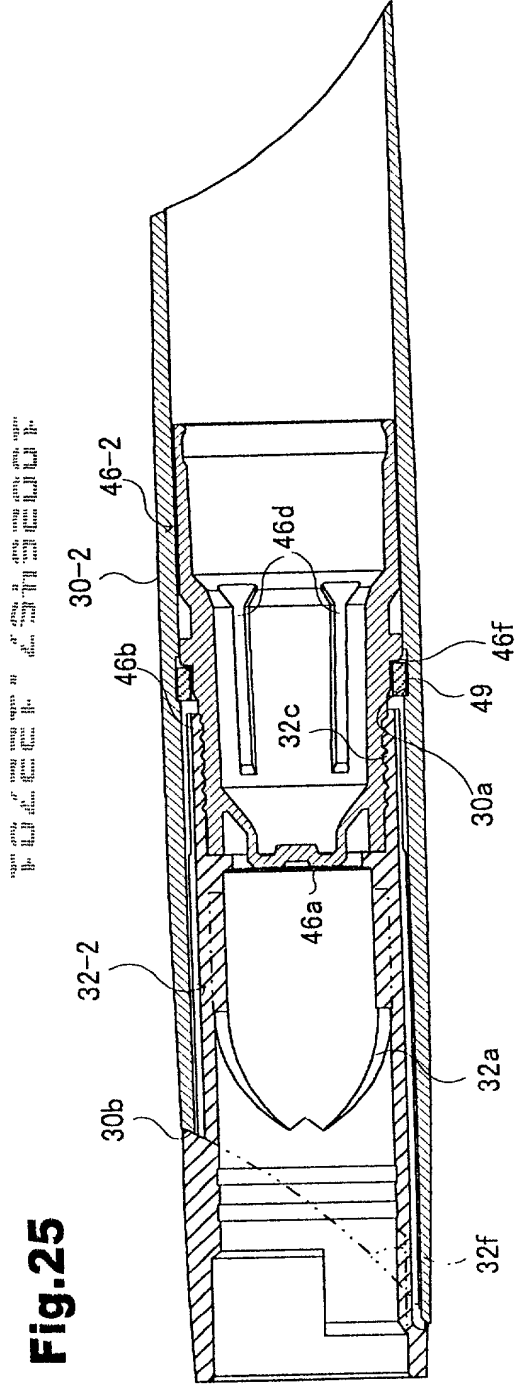
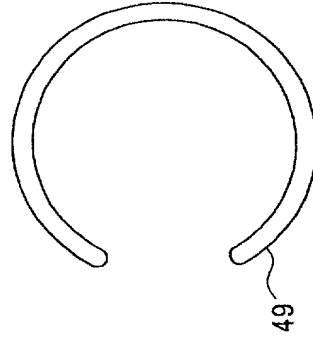
**Fi. 3.26**

Fig.27

